



**NPN BDW83, BDW83A, BDW83B,
BDW83C, BDW83D,**

NPN SILICON DARLINGTONS POWER TRANSISTORS

They are silicon epitaxial-base NPN power monolithic Darlington transistor mounted in Jedec TO-218 plastic package.

They are intended for use in power linear and switching applications.

The complementary are BDW84, BDW84A, BDW84B, BDW84C, BDW84D

Compliance to RoHS.

ABSOLUTE MAXIMUM RATINGS

Symbol	Ratings		Value	Unit	
V_{CEO}	Collector-Emitter Voltage	$I_B = 0$	BDW83	45	V
			BDW83A	60	
			BDW83B	80	
			BDW83C	100	
			BDW83D	120	
V_{CBO}	Collector- Emitter Voltage	$I_E = 0$	BDW83	45	V
			BDW83A	60	
			BDW83B	80	
			BDW83C	100	
			BDW83D	120	
V_{EBO}	Emitter-Base Voltage	$I_C = 0$	5	V	
I_C	Collector Current		15	A	
I_B	Base Current		0.5	A	
P_t	Total Power Dissipation	25°C case temperatur	150	W	
		25°C free aire temperatur	3.5		
T_J	Junction Temperature		-65 to +150	°C	
T_{Stg}	Storage Temperature		-65 to +150	°C	

THERMAL CHARACTERISTICS

Symbol	Ratings	Value	Unit
R_{thJC}	Junction to Case Thermal Resistance	0.83	°C/W
R_{thJA}	Junction to Free Air Thermal Resistance	35.7	

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ELECTRICAL CHARACTERISTICS

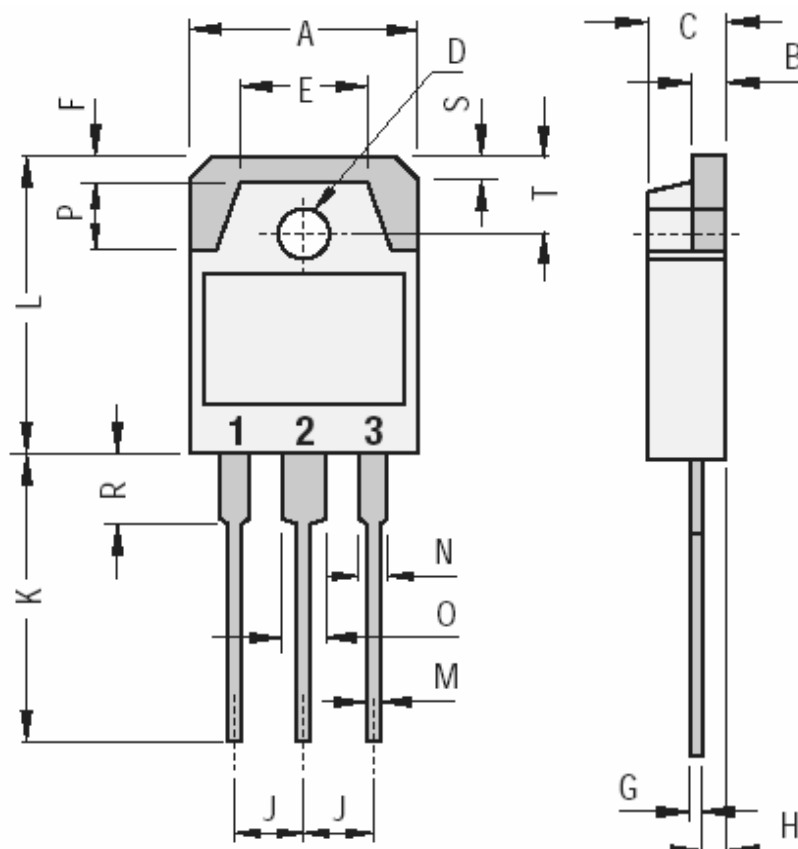
TC=25°C unless otherwise noted

Symbol	Ratings	Test Condition(s)	Min	Typ	Max	Unit	
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage (*)	$I_C=30\text{ mA}$ $I_B=0$	BDW83	45	-	-	V
			BDW83A	60	-	-	
			BDW83B	80	-	-	
			BDW83C	100	-	-	
			BDW83D	120	-	-	
I_{CEO}	Collector Cutoff Current	$I_B=0, V_{CE}=30\text{ V}$	BDW83	-	-	1	mA
			BDW83A				
			BDW83B				
			BDW83C				
			BDW83D				
I_{CBO}	Collector Cutoff Current	$I_E=0, V_{CB}=45\text{ V}$	BDW83	-	-	0.5	mA
			BDW83A				
			BDW83B				
			BDW83C				
			BDW83D				
		$I_E=0, V_{CB}=60\text{ V}$	BDW83	-	-	5	
			BDW83A				
			BDW83B				
			BDW83C				
			BDW83D				
I_{EBO}	Emitter Cutoff Current	$V_{EB}=5.0\text{ V}, I_C=0$	-	-	2	mA	
			$I_C=6\text{ A}, V_{CE}=3.0\text{ V}$	750	-	20 K	-
			$I_C=15\text{ A}, V_{CE}=3.0\text{ V}$	100	-	-	-
			$I_C=6\text{ A}, I_B=12\text{ mA}$	-	-	2.5	V
			$I_C=15\text{ A}, I_B=150\text{ mA}$	-	-	4	
$V_{BE(on)}$	Base-Emitter Voltage (*)	$I_C=6\text{ A}, I_B=3\text{ A}$	-	-	2.5		
V_{EC}	Parallel Diode Forward Voltage	$I_E=15\text{ A}, I_E=0$	-	-	3.5	V	
t_{on}	Turn-on time	$I_C=10\text{ A}, I_{B1}=-I_{B2}=40\text{ mA}$	-	0.9	-	μs	
t_{off}	Turn-off time	$R_L=3\Omega; V_{BE(off)}=-4.2\text{ V}$ Duty Cycle $\leq 2\%$	-	7	-		

(*) Pulse Duration = 300 μs , Duty Cycle $\leq 2\%$

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MECHANICAL DATA CASE TO3PN Non Isolated Plastic Package



DIMENSIONS (mm)		
	Min.	Max.
A	15.20	1600
B	1.90	2.10
C	4.60	5.00
D	3.10	3.30
E		9.60
F		2.00
G	0.35	0.55
H		1.40
J	5.35	5.55
K	20.00	
L	19.60	20.20
M	0.95	1.25
N		2.00
O		3.00
P		4.00
R		4.00
S		1.80
T	4.80	5.20

Pin 1 :	Base
Pin 2 :	Collector
Pin 3 :	Emitter

The centre pin is in electrical contact with the mounting tab.

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